SCES059D - NOVEMBER 1995 - REVISED SEPTEMBER 1999

- Member of the Texas Instruments
 Widebus™ Family
- EPIC ™ (Enhanced-Performance Implanted CMOS) Submicron Process
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JESD 17
- Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown
- Package Option Includes Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages

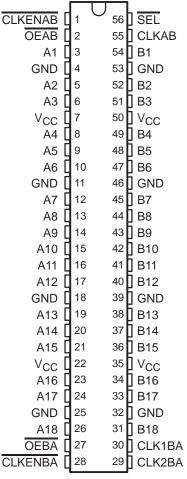
description

This 18-bit universal bus transceiver is designed for 1.65-V to 3.6-V V_{CC} operation.

Data flow in each direction is controlled by output-enable (OEAB and OEBA) and clock-enable (CLKENAB and CLKENBA) inputs. For the A-to-B data flow, the data flows through a single register. The B-to-A data can flow through a four-stage pipeline register path, or through a single register path, depending on the state of the select (SEL) input.

Data is stored in the internal registers on the low-to-high transition of the clock (CLK) input, provided that the appropriate CLKEN inputs are low. The A-to-B data transfer is synchronized to the CLKAB input, and B-to-A data transfer is synchronized with the CLK1BA and CLK2BA inputs.

DGG OR DL PACKAGE (TOP VIEW)



To ensure the high-impedance state during power up or power down, \overline{OE} should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH16525 is characterized for operation from -40°C to 85°C.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

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Function Tables

A-TO-B STORAGE $(\overline{OEAB} = L)$

II.	NPUTS	OUTPUT	
CLKENAB	CLKAB	Α	В
Н	Х	Χ	в ₀ †
L	\uparrow	L	L
L	\uparrow	Н	Н

[†] Output level before the indicated steady-state input conditions were established

B-TO-A STORAGE $(\overline{OEBA} = L)$

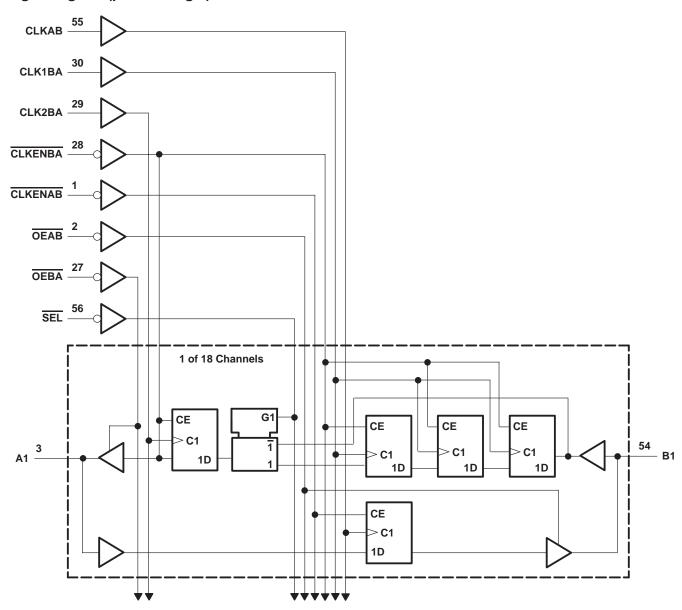
	OUTPUT				
CLKENBA	CLK2BA	CLK1BA	SEL	В	Α
Н	Х	Х	Х	Х	A ₀ †
L	\uparrow	Χ	Н	L	L
L	\uparrow	X	Н	Н	Н
L	\uparrow	\uparrow	L	L	L‡
L	\uparrow	\uparrow	L	Н	H‡

[†] Output level before the indicated steady-state input conditions were established



[‡]Three CLK1BA edges and one CLK2BA edge are needed to propagate data from B to A when SEL is low.

logic diagram (positive logic)



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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V _{CC}	
Input voltage range, V _I : Except I/O ports (see Note 1)	0.5 V to 4.6 V
I/O ports (see Notes 1 and 2)	0.5 V to V _{CC} + 0.5 V
Output voltage range, VO (see Notes 1 and 2)	0.5 V to V _{CC} + 0.5 V
Input clamp current, I _{IK} (V _I < 0)	–50 mA
Output clamp current, I _{OK} (V _O < 0)	–50 mA
Continuous output current, I _O	±50 mA
Continuous current through each V _{CC} or GND	±100 mA
Package thermal impedance, θ _{JA} (see Note 3): DGG package	81°C/W
DL package	
Storage temperature range, T _{stq}	–65°C to 150°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.
 - 2. This value is limited to 4.6 V maximum.
 - 3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT	
VCC	Supply voltage		1.65	3.6	V	
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	0.65 × V _{CC}			
V_{IH}	High-level input voltage	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.7		V	
	IH High-level input voltage Low-level input voltage I Input voltage O Output voltage High-level output current	V _{CC} = 2.7 V to 3.6 V	2			
		V _{CC} = 1.65 V to 1.95 V		0.35 × V _{CC}		
V_{IL}	Low-level input voltage	V _{CC} = 2.3 V to 2.7 V		0.7	V	
		V _{CC} = 2.7 V to 3.6 V		0.8		
٧ _I	Input voltage	-	0	VCC	V	
٧o	Output voltage		0	VCC	V	
		V _{CC} = 1.65 V		-4		
1	/IL Low-level input voltage /I Input voltage /O Output voltage OH High-level output current OL Low-level output current	V _{CC} = 2.3 V		-12		
ЮН		V _{CC} = 2.7 V		-12	mA	
		V _{CC} = 3 V		-24		
		V _{CC} = 1.65 V		4		
1	Lave lavel autout aurora	V _{CC} = 2.3 V		12		
IOL	Low-level output current	V _{CC} = 2.7 V		12	mA	
		V _{CC} = 3 V	24			
Δt/Δν	Input transition rise or fall rate	-		10	ns/V	
ТД	Operating free-air temperature		-40	85	°C	

NOTE 4: All unused control inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.



electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARA	AMETER	TEST C	ONDITIONS	vcc	MIN	TYP†	MAX	UNIT
		I _{OH} = -100 μA		1.65 V to 3.6 V	V _{CC} -0.	.2		
$VOH \begin{tabular}{ll} I_{OH} = -100 \ \mu A & 1.65 \ V \ to 3.6 \ V & V_{CC}-0.2 \\ I_{OH} = -4 \ mA & 1.65 \ V & 1.2 \\ I_{OH} = -6 \ mA & 2.3 \ V & 2 \\ \hline & 2.3 \ V & 1.7 \\ \hline & 2.7 \ V & 2.2 \\ \hline & 3 \ V & 2.4 \\ \hline & 1_{OH} = -24 \ mA & 3 \ V & 2 \\ \hline & I_{OL} = 100 \ \mu A & 1.65 \ V \ to 3.6 \ V \\ \hline & I_{OL} = 4 \ mA & 1.65 \ V \ to 3.6 \ V \\ \hline & I_{OL} = 6 \ mA & 2.3 \ V \\ \hline & I_{OL} = 6 \ mA & 2.3 \ V \\ \hline & I_{OL} = 12 \ mA & 3 \ V & 0.0 \\ \hline & I_{OL} = 12 \ mA & 3 \ V & 0.0 \\ \hline & I_{OL} = 100 \ \mu A & 3.6 \ V \\ \hline & I_{OL} = 100 \ mA & 2.3 \ V \\ \hline & I_{OL} = 100 \ mA & 2.3 \ V \\ \hline & I_{OL} = 100 \ mA & 3.6 \ V \\ \hline & I_{OL} = 100 \ mA & 3.6 \ V \\ \hline & I_{OL} = 100 \ mA & 3.6 \ V \\ \hline & I_{OL} = 100 \ V_{OL} & 3.6 \ V \\ \hline & I_{OL} = 100 \ V_{OL} & 3.6 \ V \\ \hline & I_{OL} = 100 \ V_{OL} & 3.6 \ V \\ \hline & I_{OL} = 100 \ V_{OL} & 3.6 \ V \\ \hline & I_{OL} = 100 \ V_{OL} & 3.6 \ V \\ \hline & I_{OL} = 100 \ V_{OL} & 3.6 \ V \\ \hline & I_{OL} = 100 \ V_{OL} & 3.6 \ V \\ \hline & I_{OL} = 100 \ V_{OL} & 3.6 \ V \\ \hline & I_{OL} = 100 \ V_{OL} & 3.6 \ V \\ \hline & I_{OL} = 100 \ V_{OL} & 3.6 \ V \\ \hline & I_{OL} = 100 \ V_{OL} & 3.6 \ V \\ \hline & I_{OL} = 100 \ V_{OL} & 0.0000000000000000000000000000000000$		1.65 V	1.2					
	2.3 V	2						
		V						
		I _{OH} = -12 mA		2.7 V	2.2			
				3 V	2.4			
		I _{OH} = -24 mA		3 V	2			
		I _{OL} = 100 μA		1.65 V to 3.6 V			0.2	
$\begin{tabular}{ c c c c c c c c c c c c c c c c c c c$			0.45					
$VOH \begin{tabular}{ll} $I_{OH} = -4 \text{ mA} \\ $I_{OH} = -6 \text{ mA} \\ \end{tabular}$ $VOH \begin{tabular}{ll} $I_{OH} = -12 \text{ mA} \\ \end{tabular}$ $I_{OH} = -12 \text{ mA} \\ \end{tabular}$ $I_{OL} = 100 \mu\text{A} \\ I_{OL} = 4 \text{ mA} \\ \end{tabular}$ $I_{OL} = 6 \text{ mA} \\ \end{tabular}$ $I_{OL} = 12 \text{ mA} \\ \end{tabular}$ $I_{OL} = 24 \text{ mA} \\ \end{tabular}$ $I_{OL} = 24 \text{ mA} \\ \end{tabular}$ $V_{I} = V_{CC} \text{ or GND} \\ V_{I} = 0.58 \text{ V} \\ V_{I} = 0.7 \text{ V} \\ V_{I} = 0.7 \text{ V} \\ V_{I} = 0.7 \text{ V} \\ V_{I} = 0.8 \text{ V} \\ V_{I} = 2 \text{ V} \\ V_{I} = 0 \text{ to } 3.6 \text{ V}^{\ddagger} \\ \end{tabular}$ I_{OZ} I_{OZ} $V_{O} = V_{CC} \text{ or GND} \\ V_{I} = V_{CC} \text{ or GND} \\ One \text{ input at } V_{CC} = 0.6 \text{ V} \\ \end{tabular}$		2.3 V			0.4	V		
	lo. – 12 mA	2.3 V			0.7	V		
		IOL = 12 IIIA	2.7 V			0.4		
$VOL \begin{tabular}{ c c c c c c c c c c c c c c c c c c c$				0.55				
IĮ		$V_I = V_{CC}$ or GND		3.6 V			±5	μΑ
		V _I = 0.58 V		1.65 V	25			
		V _I = 1.07 V		1.65 V	-25			
		V _I = 0.7 V		2.3 V	45			
II(hold)		V _I = 1.7 V		2.3 V	-45			μΑ
		V _I = 0.8 V		3 V	75			
		V _I = 2 V		3 V	-75			
		$V_{I} = 0 \text{ to } 3.6 \text{ V}^{\ddagger}$		3.6 V			±500	
l _{OZ} §		$V_O = V_{CC}$ or GND		3.6 V			±10	μΑ
lcc		$V_I = V_{CC}$ or GND,	I _O = 0	3.6 V			40	μΑ
ΔlCC		One input at V _{CC} – 0.6 V,	Other inputs at V _{CC} or GND	3 V to 3.6 V			750	μΑ
Ci	Control inputs	$V_I = V_{CC}$ or GND		3.3 V		3		pF
Cio	A or B ports	$V_O = V_{CC}$ or GND		3.3 V		7		pF

[†] All typical values are at V_{CC} = 3.3 V, T_A = 25°C. ‡ This is the bus-hold maximum dynamic current. It is the minimum overdrive current required to switch the input from one state to another.

 $[\]mbox{\$ For I/O ports, the parameter IOZ includes the input leakage current.}$

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timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 through 3)

		V _{CC} =	1.8 V	V _{CC} =		VCC =	2.7 V	V _{CC} =		UNIT	
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
fclock	Clock frequency			†		120		125		150	MHz
t _W	Pulse duration, CLk	high or low	†		3.2		3.2		3		ns
		A data before CLKAB↑	†		1.3		1.3		1.3		
t _{SU} So		B data before CLK2BA↑	†		2.1		1.8		1.7		
		B data before CLK1BA↑	†		1.3		1.2		1.1		
	Setup time	SEL before CLK2BA↑	†		3.3		3.3		3.3		ns
		CLKENAB before CLKAB↑	†		2.1		1.9		1.6		
		CLKENBA before CLK1BA↑	†		2.7		2.5		2.1		
		CLKENBA before CLK2BA↑	†		2.7		2.5		2.2		
		A data after CLKAB↑	†		0.7		0.4		0.9		
	B data after CLK2BA↑	†		0.4		0		0.6			
		B data after CLK1BA↑	†		0.8		0.4		1		
th	Hold time	SEL after CLK2BA↑	†		0		0		0.1		ns
''		CLKENAB after CLKAB↑	†		0.1		0.3		0.3		
		CLKENBA after CLK1BA↑	†		0		0		0.1		
		CLKENBA after CLK2BA↑	†		0		0		0		

[†] This information was not available at the time of publication.

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 through 3)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} = 1.8 V		1.8 V V _{CC} = 2 ± 0.2 V		V _{CC} = 2.5 V ± 0.2 V		V _{CC} = 2.7 V		V _{CC} = 3.3 V ± 0.3 V		UNIT
	(INFOT)	(001F01)	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX			
f _{max}			†		120		125		150		MHz		
t _{pd}	CLKAB or CLK2BA	A or B		†	1	4.5		4.4	1	4.2	ns		
t _{en}	OEAB or OEBA	A or B		†	1	6.1		6.1	1	5.1	ns		
^t dis	OEAB or OEBA	A or B		†	1	6.3		5.4	1	4.9	ns		

[†] This information was not available at the time of publication.

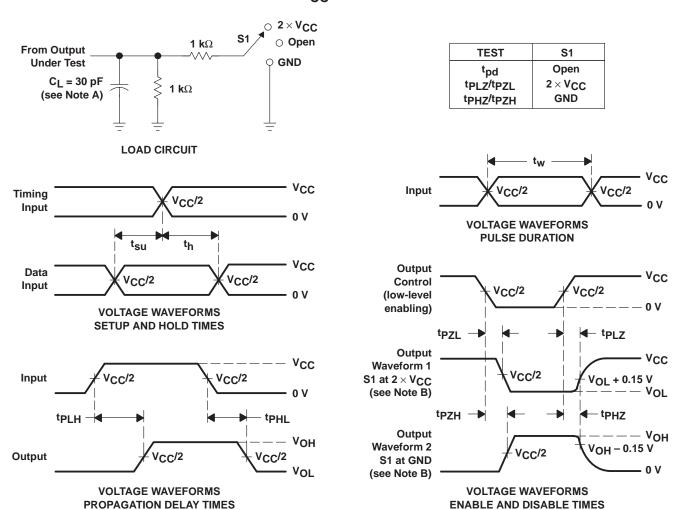
operating characteristics, T_A = 25°C

PARAMETER		PARAMETER TEST CONDITIONS				V _{CC} = 3.3 V	UNIT
	TANAMILTLIN		1231 CONDITIONS	TYP TYP TYP		ONIT	
<u> </u>	Power dissipation	Outputs enabled	C ₁ = 50 pF. f = 10 MHz	†	160	160	nE.
Cpd	capacitance	Outputs disabled	$C_L = 50 \text{ pr}, f = 10 \text{ MHz}$	†	160	160	pF

[†] This information was not available at the time of publication.



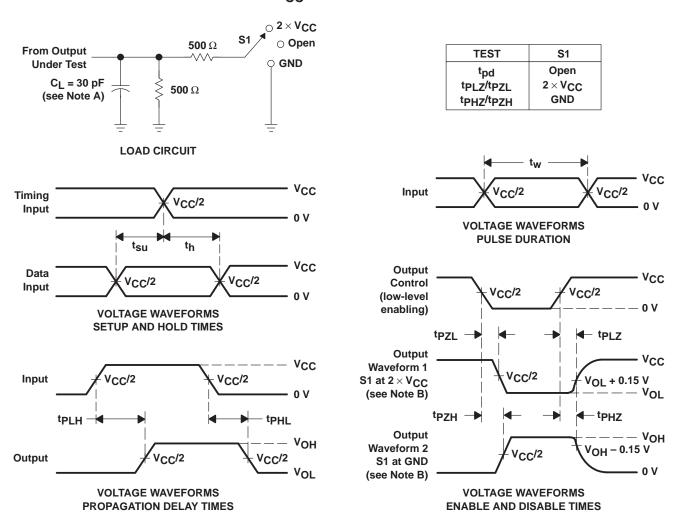
PARAMETER MEASUREMENT INFORMATION V_{CC} = 1.8 V



- NOTES: A. C_L includes probe and jig capacitance.
 - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
 - C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_O = 50 Ω , $t_f \leq$ 2 ns.
 - D. The outputs are measured one at a time with one transition per measurement.
 - E. tpLz and tpHz are the same as tdis.
 - F. tpzL and tpzH are the same as ten.
 - G. tpLH and tpHL are the same as tpd.

Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION $V_{CC} = 2.5 \text{ V} \pm 0.2 \text{ V}$



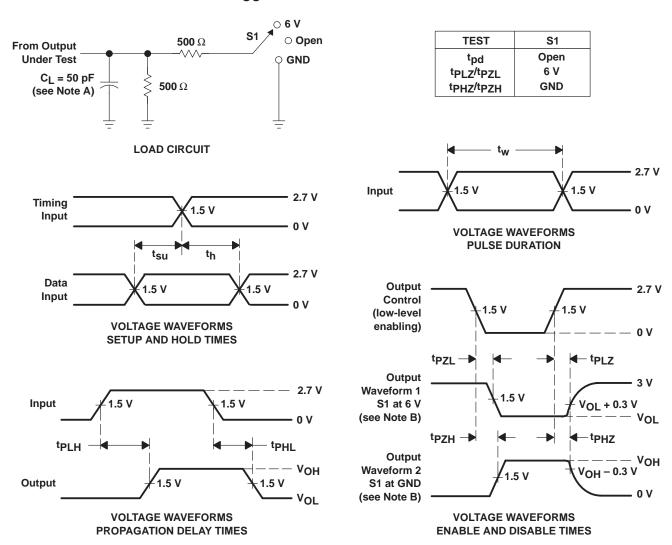
NOTES: A. C_I includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_Q = 50~\Omega$, $t_f \leq$ 2 ns, $t_f \leq$ 2 ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpl 7 and tpH7 are the same as tdis.
- F. tpzL and tpzH are the same as ten.
- G. tpLH and tpHL are the same as tpd.

Figure 2. Load Circuit and Voltage Waveforms



PARAMETER MEASUREMENT INFORMATION V_{CC} = 2.7 V AND 3.3 V \pm 0.3 V



NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_Q = 50 \Omega$, $t_f \leq 2.5 \text{ ns.}$
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpLZ and tpHZ are the same as tdis.
- F. tpzi and tpzH are the same as ten.
- G. tpLH and tpHL are the same as tpd.

Figure 3. Load Circuit and Voltage Waveforms



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